Title of your presentation for WINDS 2017
(Times New Roman, 14pt, bold)

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The Workshop on Innovative Nanoscale Devices and Systems will be held from Nov. 26 to Dec. 1, 2017, at the Hapuna Beach Prince Hotel on the Kohala Coast of the Big Island of Hawaii [1]. The abstract text should fit in one A4 page (210 mm x 297 mm, portrait, printable area 160 mm x 240 mm – top/bottom margins of 30 mm and left/right margins of 25 mm). An additional page is allowed for figures (see the second page of this template for the suggested format). Please underline the presenting author. Ensure that the e-mail address is correct, as it is used for further communications. Please do **not** insert any page number, header or footer. Please use Times New Roman font and do not forget to remove all ( )'s for instruction. Save your abstract as a **single pdf** (Portable Document Format) **file** with the file name, (presenter's first name)_(presenter's family name).pdf. For example, when the presenter is Akinobu Kanda, the file name is akinobu_kanda.pdf. If you submit more than one abstract as presenter, you may add a number at the end of the file name (e.g., akinobu_kanda _2.pdf). Make sure that the pdf file of your abstract is of camera-ready quality with all fonts embedded.
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[1] H. Tomori et al., Appl. Phys. Express, **4**, 075102 (2011).
(Times New Roman, 11pt)

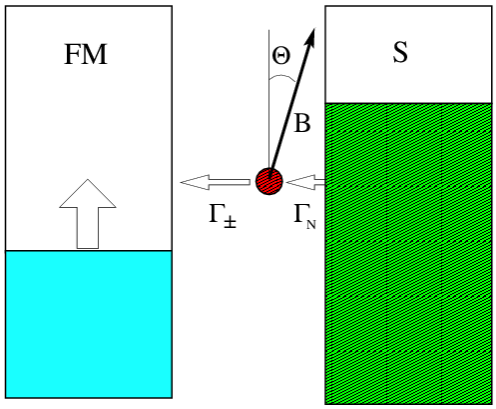

*Fig.1: The trap is connected to electrodes with the rates Γ_N and $\Gamma_\pm$. A magnetic field **B** defines the trap spin quantization axis OZ' at an angle Θ to the magnetization orientation OZ in the ferromagnet.*

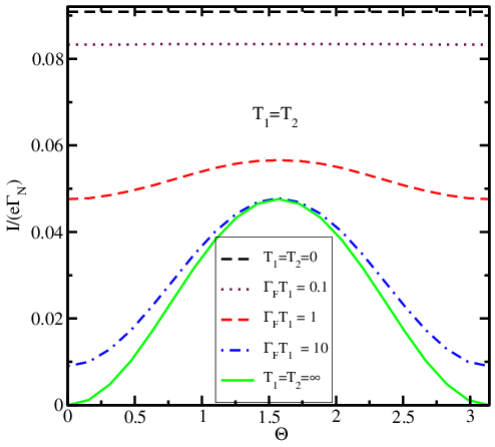

Fig.2: Current in units of $e\Gamma_N$ as a function of Θ for p=1, Γ_N/Γ_F = 10, ω_L/Γ_F = 1, and several values of T_2=T_1.

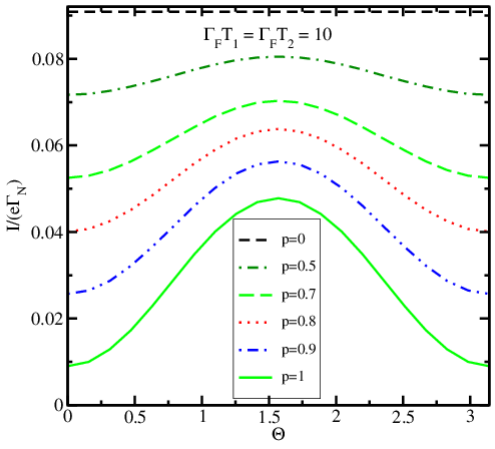

Fig.3: Current as a function of Θ, for Γ_N/Γ_F = 10, ω_L/Γ_F = 1, $\Gamma_F T_1$ = $\Gamma_F T_1$ = 10, and several values of p.

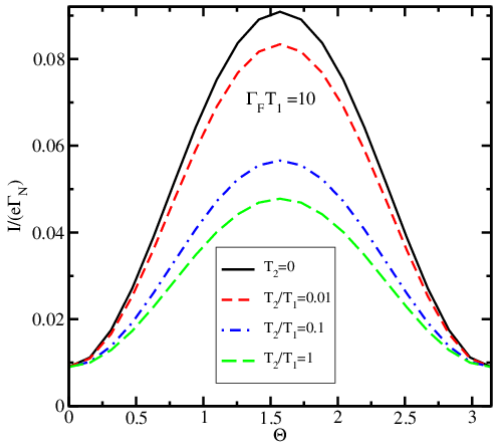

Fig.4: Current as a function of Θ, for p=1, Γ_N/Γ_F = 10, ω_L/Γ_F = 1, $\Gamma_F T_1$ = 10, and several values of T_2/T_1.

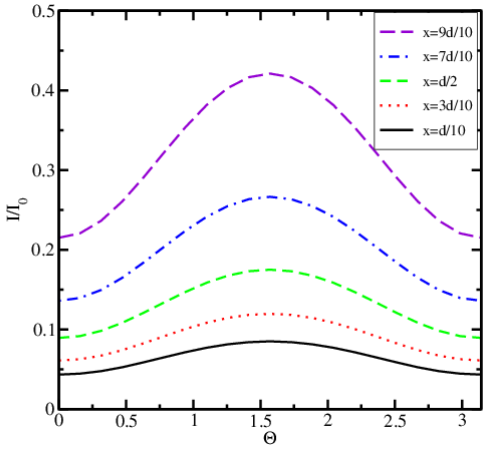

Fig.5 Normalized current as a function of the position x relative to silicon, for p=1, Γ_N=Γ_0 exp(-x/d) , Γ_F=Γ_0 exp(-(d-x)/d), T_2=T_1, $\omega_L T_2$ = $\Gamma_0 T_2$ =10,

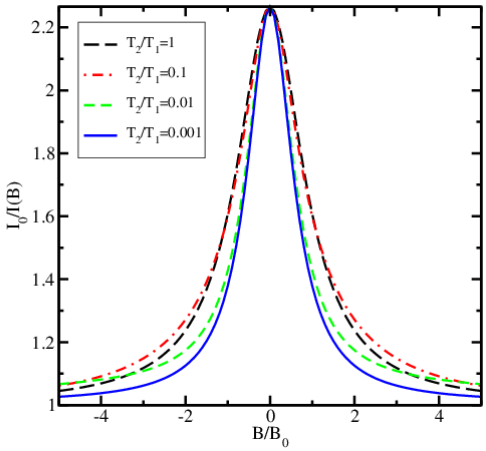

*Fig.6: Magnetoresistance signal as a function of the perpendicular magnetic field **B** for several T_2/T_1, for p=0.8 and $\Gamma_F T_1$ = 10. The field $\mathbf{B}_0$ is parallel to the magnetization in the ferromagnet.*